

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT	<i>Complete if Known</i>	
	Application Number	10/759,081 RECEIVED
	Filing Date	January 20, 2004 CENTRAL FAX CENTER
	First Named Inventor	Dr. Chou H. Li NOV 01 2006
	Group Art Unit	2815
	Examiner Name	William F. Kraig
Sheet 1 of 5	Attorney Docket Number	2480.202

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	AA	3,283,171		Seeds	11-01-1966
	AB	3,585,714		Li	06-22-1971
	AC	3,752,711		Kooi, et al.	08-14-1973
	AD	3,098,160		Noyce	07-16-1963
	AE	3,233,305		Dill	02-08-1966
	AF	3,386,865		Doo	06-04-1968
	AG	3,360,696		Neilson, et al.	12-26-1967
	AH	3,411,051		Kilby	11-12-1968
	AI	3,426,253		LaRocque, et al.	02-04-1969
	AJ	3,648,125		Peltzer	03-07-1972
	AK	3,970,486		Kool	07-20-1976
	AL	3,345,222		Nomura, et al.	10-03-1967
	AM	3,440,717		Hill	04-28-1969
	AN	3,492,174		Nakamura, et al.	01-27-1970
	AO	3,520,139		Elkind, et al.	07-14-1970
	AP	3,515,956		Martin, et al.	06-02-1970

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code.

⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached. AB Indicates that only an English language abstract is attached.

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		Number	Kind Code ² (if known)		
	AQ	3,581,161		Cunningham, et al.	05-25-1971
	AR	3,586,542		MacRae	06-22-1971
	AS	3,209,428		Barbaro	10-05-1965
	AT	4,139,442		Bondur, et al.	02-13-1979
	AU	5,254,218		Roberts, et al.	10-19-1993
	AV	3,321,340		Murphy	05-23-1967
	AW	3,430,109		Li	02-25-1969
	AX	3,622,382		Brack, et al.	11-23-1971
	AY	4,916,513		Li	04-10-1990
	AZ	5,040,034		Murakami, et al.	08-13-1991
	BA	5,082,793		Li	01-21-1992
	BB	3,376,172		Byczkowski	04-02-1968
	BC	3,755,001		Kooi, et al.	08-28-1973
	BD	3,982,315		Kubo	09-28-1976
	BE	RE 28653		Murphy	12-16-1975
	BF	3,852,104		Kooi, et al.	12-03-1974
	BG	4,101,344		Kooi, et al.	07-18-1978

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	BH	2,911,706		Wertwijn	11-10-1959
	BI	2,980,830		Shockley	04-18-1961
	BJ	3,136,897		Kaufman	06-09-1964
	BK	5,361,326		Aparicio, IV, et al.	11-01-1994

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office ³	Number ⁴	Kind ⁵ Code (if known)			
	BL	GB	1086607			10-1967	
	BM	JP	S34-2529			04-16-1959	
	BN	GB	1214203			12-02-1970	

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
	BO	"Integrated Circuits Design Principles and Fabrication," McGraw-Hill Book Co., Inc., 1965, pp. 127-31; 145-50; 174-85; Fig. 5-4(a), p. 131; Fig. 5-23, p. 146; Fig. 5-25 -5-27, pp. 147-48; Fig. 7-1, p. 175; Fig. 7-2, p. 176; Fig. 7-6(a), p. 179.	
	BP	"New Isolation Method Shrinks Bipolar Ics," Electronics, McGraw-Hill, Mar. 1, 1971, pp. 52-55, Fig. 5-6, p. 55.	
	BQ	"Diffusion Depths in Silicon Measured Using Cylindrical Grooves," The American Physical Society Abstracts from the Epitome of the 1956 Monterey Meeting, Session H, Nov. 1956.	
	BR	McDonald, et al., "Measurement of the Depth of Diffused Layers in Silicon By the Grooving Method," Journal of the Electrochemical Society, Vol. 109, No. 2, Feb. 1962. pp. 141-144 – see Fig. 2 and p. 143.	
	BS	Jones, R.E. and Doo, Y., "A Composite Insulator-Junction Isolation," Electrochemical Technology, May-June 1967.	
	BT	Breener, S.S., "The Growth of Whiskers by the Reduction of Metal Salts," Acta Metallurgica, Vol. 4, Jan. 1956, pp. 62-74.	
	BU	Stiles, P.J., et al., "Schottky Barrier Diode", IBM Technical Disclosure Bulletin, Vol. 11 No. 1, June 1968, p. 20.	
	BV	Doo, Y., et al., "Making Monolithic Semiconductor Structures for Integrated Circuits Using Composite Insulation and Junction Isolation Techniques," IBMS Technical Disclosure Bulletin, Vol. 8 No. 4, Sept. 1965, pp. 659-660.	
	BW	Phillips, A.B., "Transistor Engineering," McGraw-Hill, 1962, pp. 111-115.	
	BX	Burrill, J.T., et al., "Ion Implantation as a Production Technique," IEEE Transactions on Electron Devices, Vol. Ed-14, No. 1, Jan. 1967, pp. 10-17.	
	BY	Buchanan, B., et al., "High Energy (1 to 2.5 Mev) Ion Implantation For Obtaining Novel Semiconductor Junction Structures," Air Force Cambridge Res. Labs., Off. Of Aerospace Research, Bedford, MA, pp. 649-684.	
	BZ	Gibbons, J.F., "Ion Implantation in Semiconductors-Part I Range Distribution Theory and Experiments," Proceedings of the IEEE, Vol. 56, No.3, March 1968, pp. 295-318.	

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	CA	NOTES, Solid-State Electronics, Pergamon Press, 1967, Vol. 10, pp. 1105-1108, Printed in Great Britain.	
	CB	Kennedy, D.P., et al., "Calculations of Impurity Atom Diffusion Through a Narrow Diffusion Mask Opening," IBM Journal, Jan. 1966, pp. 6-12.	
	CC	Appels, J.A., et al., "Local Oxidation of Silicon and Its Application in Semiconductor-Device Technology, Philips Res. Repts. 25, 1970, pp. 118-132.	
	CD	Doo, V.Y., "Silicon Nitride, A New Diffusion Mask, IEEE Transactions on Electron Devices, Vol. Ed.-13, No. 7, July 1966, pp. 561-563.	
	CE	S.S. Brenner, "The Growth of Whiskers by the Reduction of Metal Salts", Acta Metallurgica, Vol. 4 (January 1956) pp. 62-74.	

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CERTIFICATE OF FACSIMILE

I hereby certify that this paper is being facsimile transmitted to Examiner William F. Kraig, Art Unit 2815, at the U.S. Patent and Trademark Office, Fax No. (571) 273-8300 on November 1, 2006.


Keith R. Lange
Reg. 44,201PATENT
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	
)	
Dr. Chou H. Li)	Examiner: William F. Kraig
)	
Appl. No.: 10/759,081)	Art Unit: 2815
)	
Filed: January 20, 2004)	Atty. Dkt. No.: 2480.202
)	
For: INTEGRATED CIRCUIT)	
DEVICE)	

MAIL STOP AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In fulfillment of the requirements of candor and good faith set forth in 37 C.F.R. §1.56, Applicant submits herewith the following Information Disclosure Statement in accordance with the provisions of 37 C.F.R. §§1.97 and 1.98 for the above-referenced patent application.

As this Information Disclosure Statement is being filed within three months of the filing date of a Request for Continued Examination, it is deemed to be timely filed, and accordingly no fee is believed to be due. However, if

Applicant is incorrect in this regard, you are hereby authorized to charge any such fee, or credit any overpayments, to Deposit Account No. 50-0644, and are respectfully requested to notify the undersigned of any such charge or credit.

U.S. PATENT DOCUMENTS

<u>U.S. PATENT/ APPL. PUBL. NO.</u>	<u>PATENTEE/ APPLICANT</u>	<u>ISSUE/PUBLICATION DATE (MM-DD-YYYY)</u>
3,283,171	Seeds	11-01-1966
3,585,714	Li	06-22-1971
3,752,711	Kooi, et al.	08-14-1973
3,098,160	Noyce	07-16-1963
3,233,305	Dill	02-08-1966
3,386,865	Doo	06-04-1968
3,360,696	Neilson, et al.	12-26-1967
3,411,051	Kilby	11-12-1968
3,426,253	LaRocque, et al.	02-04-1969
3,648,125	Peltzer	03-07-1972
3,970,486	Kooi	07-20-1976
3,345,222	Nomura, et al.	10-03-1967
3,440,717	Hill	04-29-1969
3,492,174	Nakamura, et al.	01-27-1970
3,520,139	Elkind, et al.	07-14-1970
3,515,956	Martin, et al.	06-02-1970
3,581,161	Cunningham, et al.	05-25-1971
3,586,542	MacRae	06-22-1971
3,209,428	Barbaro	10-05-1965
4,139,442	Bondur, et al.	02-13-1979

5,254,218	Roberts, et al.	10-19-1993
3,321,340	Murphy	05-23-1967
3,430,109	Li	02-25-1969
3,622,382	Brack, et al.	11-23-1971
4,916,513	Li	04-10-1990
5,040,034	Murakami, et al.	08-13-1991
5,082,793	Li	01-21-1992
3,376,172	Byczkowski	04-02-1968
3,755,001	Kooi, et al.	08-28-1973
3,982,315	Kubo	09-28-1976
RE 28653	Murphy	12-16-1975
3,852,104	Kooi, et al.	12-03-1974
4,101,344	Kooi, et al.	07-18-1978
2,911,706	Wertwijn	11-10-1959
2,980,830	Shockley	04-18-1961
3,136,897	Kaufman	06-09-1964
5,361,326	Aparicio, IV, et al.	11-01-1994

FOREIGN PATENT DOCUMENTS

<u>COUNTRY</u> <u>CODE</u>	<u>PATENT/</u> <u>APPL. PUBL. NO.</u>	<u>ISSUE/PUBLICATION</u> <u>DATE (MM-DD-YYYY)</u>
GB	1086607	10-1967
JP	S34-2529	04-16-1959
GB	1214203	12-02-1970

NON-PATENT LITERATURE DOCUMENTS

"Integrated Circuits Design Principles and Fabrication,"
McGraw-Hill Book Co., Inc., 1965, pp. 127-31; 145-50; 174-

85; Fig. 5-4(a), p. 131; Fig. 5-23, p. 146; Fig. 5-25 -5-27, pp. 147-48; Fig. 7-1, p. 175; Fig. 7-2, p. 176; Fig. 7-6(a), p. 179.

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Stiles, P.J., et al., "Schottky Barrier Diode", IBM Technical Disclosure Bulletin, Vol. 11 No. 1, June 1968, p. 20.

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Phillips, A.B., "Transistor Engineering," McGraw-Hill, 1962, pp. 111-115.

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Buchanan, B., et al., "High Energy (1 to 2.5 Mev) Ion Implantation For Obtaining Novel Semi-Conductor Junction Structures," Air Force Cambridge Res. Labs., Off. Of Aerospace Research, Bedford, MA, pp. 649-684.

Gibbons, J.F., "Ion Implantation in Semiconductors-Part I Range Distribution Theory and Experiments," Proceedings of the IEEE, Vol. 56, No.3, March 1968, pp. 295-318.

Solid-State Electronics, Pergamon Press, 1967, Vol. 10, pp. 1105-1108, Printed in Great Britain.

Kennedy, D.P., et al., "Calculations of Impurity Atom Diffusion Through a Narrow Diffusion Mask Opening," IBM Journal, Jan. 1966, pp. 6-12.

Appels, J.A., et al., "Local Oxidation of Silicon and Its Application in Semiconductor-Device Technology", Philips Res. Repts. 25, 1970, pp. 118-132.

Doo, V.Y., "Silicon Nitride, A New Diffusion Mask", IEEE Transactions on Electron Devices, Vol. Ed.-13, No. 7, July 1966, pp. 561-563.

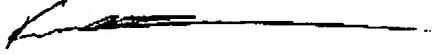
S.S. Brenner, "The Growth of Whiskers by the Reduction of Metal Salts", Acta Metallurgica, Vol. 4 (January 1956) pp. 62-74.

As provided by 37 C.F.R. §1.98(d)(1), Applicant has not provided copies of any of the above-references, as it is believed that each was submitted in parent application 08/483,938, now U.S. Patent No. 7,038,290, to which the present application claims priority, but will do so upon request of the Office.

Each of the above-cited references are listed on Applicant's enclosed Substitute Form PTO-1449. The Examiner is respectfully requested to acknowledge consideration of each reference listed thereon by initialing in the designated area and returning a copy of same to Applicant.

Please direct any questions concerning this matter to Applicant's undersigned representative, who can be reached directly at (610) 869-6302.

Respectfully submitted,
HALL, VANDE SANDE & PEQUIGNOT, LLP
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